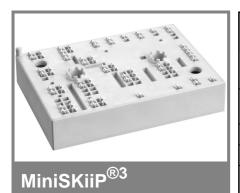
# SKiiP 39AC12T4V1



3-phase bridge inverter

SKiiP 39AC12T4V1

**Target Data** 

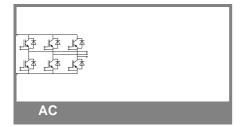
#### **Features**

- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

## **Typical Applications**

<b>Absolute Maximum Ratings</b> T <sub>s</sub> = 25 °C, unless otherwise specified						
Symbol	Conditions			Values	Units	
IGBT						
$V_{CES}$	T <sub>j</sub> = 25 °C			1200	V	
I <sub>C</sub>	T <sub>j</sub> = 175 °C	T <sub>c</sub> = 25 °C		171	Α	
		$T_c = 70  ^{\circ}C$		135	Α	
I <sub>CRM</sub>	$I_{CRM} = 3xI_{Cnom}$			450	Α	
$V_{GES}$				±20	V	
t <sub>psc</sub>	$V_{CC}$ = 600 V; $V_{GE} \le 20$ V; $V_{CES} < 1200$ V	T <sub>j</sub> = 150 °C		10	μs	
Inverse D	Piode		•		•	
I <sub>F</sub>	T <sub>j</sub> = 175 °C	$T_c = 25 ^{\circ}C$		144	Α	
		$T_c = 70 ^{\circ}C$		128	Α	
$I_{FRM}$	$I_{CRM} = 3xI_{Cnom}$			450	Α	
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms; sin	T <sub>j</sub> = 150 °C		900	Α	
Module						
$I_{t(RMS)}$				160	Α	
$T_{vj}$				-40+175	°C	
T <sub>stg</sub>				-40+125	°C	
V <sub>isol</sub>	AC, 1 min.			2500	V	

Characteristics $T_s =$		25 $^{\circ}\text{C},$ unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 6 \text{ mA}$		5	5,8	6,5	V
I <sub>CES</sub>	$V_{GE} = V, V_{CE} = V_{CES}$	$T_j = ^{\circ}C$				mA
$V_{CE0}$		T <sub>j</sub> = 25 °C		1,1	1,3	V
		T <sub>j</sub> = 150 °C		1	1,2	V
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C		5	5	mΩ
		$T_j = 150$ °C		8,3	8,3	mΩ
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 150 A, V <sub>GE</sub> = 15 V			1,8	2	V
		$T_j = 150^{\circ}C_{chiplev.}$		2,2	2,4	V
C <sub>ies</sub>						nF
C <sub>oes</sub>	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz				nF
C <sub>res</sub>						nF
$R_{Gint}$	T <sub>j</sub> = 25 °C			5		Ω
$t_{d(on)}$						ns
t,	R <sub>Gon</sub> =	V <sub>CC</sub> = V		0		ns
E <sub>on</sub>	D =	$I_{Cnom} = A$ $T_i = {^{\circ}C}$		9		mJ ns
${f t}_{\sf d(off)} \ {f t}_{\sf f}$	R <sub>Goff</sub> =	V <sub>GE</sub> = ±15V				ns
E <sub>off</sub>		GE .		21		mJ
R <sub>th(j-s)</sub>	per IGBT	•		0,33		K/W



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**Target Data** 

### **Features**

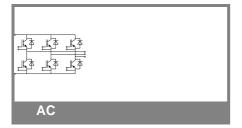
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### **Typical Applications**

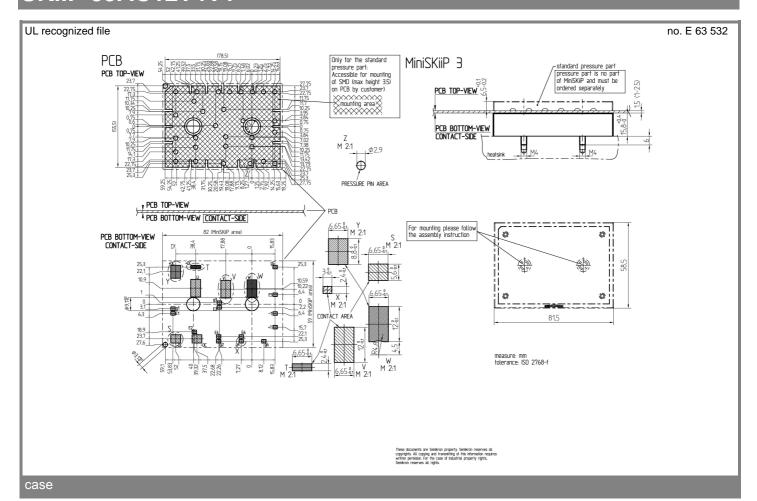
Characteristics							
Symbol	Conditions	ĺ	min.	typ.	max.	Units	
Inverse Diode							
$V_F = V_{EC}$	I <sub>Fnom</sub> = 150 A; V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25 °C <sub>chiplev</sub> .		2,15	2,45	V	
		T <sub>j</sub> = 150 °C <sub>chiplev.</sub>		2,05	2,4	V	
$V_{F0}$		T <sub>j</sub> = 25 °C		1,3	1,5	V	
		T <sub>j</sub> = 150 °C		0,9	1,1	V	
r <sub>F</sub>		T <sub>j</sub> = 25 °C		5,7	6,3	mΩ	
		T <sub>j</sub> = 150 °C		7,7	8,6	$m\Omega$	
I <sub>RRM</sub>	I <sub>Fnom</sub> = 150 A	T <sub>j</sub> = 150 °C				Α	
$Q_{rr}$						μC	
E <sub>rr</sub>	$V_{GE} = \pm 15V$			11,3		mJ	
$R_{th(j-s)}$	per diode			0,4		K/W	
M <sub>s</sub>	to heat sink		2		2,5	Nm	
w				95		g	
Temperat	ure sensor						
R <sub>ts</sub>	3%, Tr = 25°C			1000		Ω	
R <sub>ts</sub>	3%, Tr = 100°C			1670		Ω	

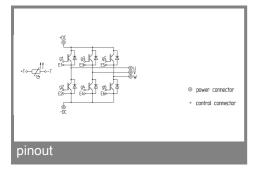
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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